

# 2SD0638 (2SD638)

## Silicon NPN epitaxial planar type

For medium-power general amplification

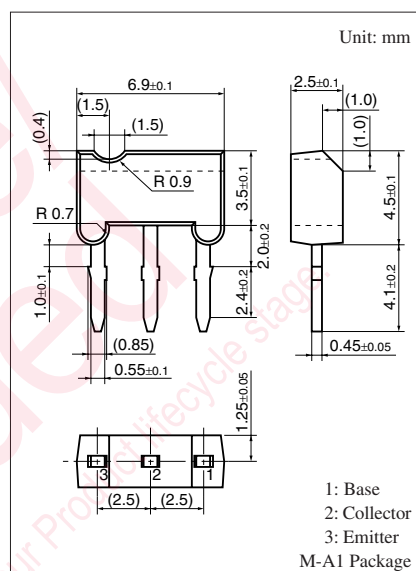
Complementary to 2SB0643 (2SB643)

### ■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	30	V
Collector-emitter voltage (Base open)	$V_{CEO}$	25	V
Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
Collector current	$I_C$	0.5	A
Peak collector current	$I_{CP}$	1	A
Collector power dissipation *	$P_C$	600	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

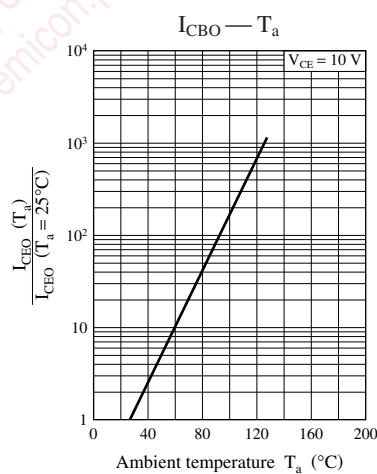
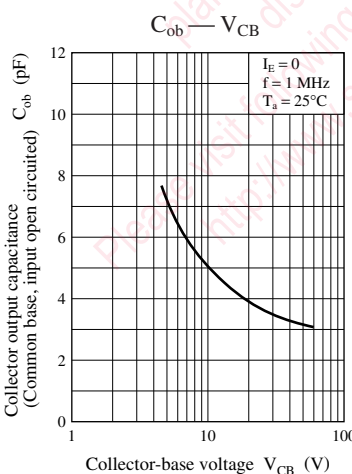
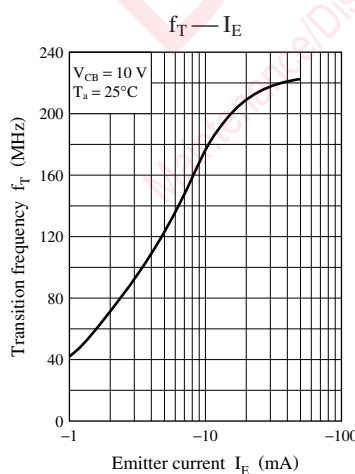
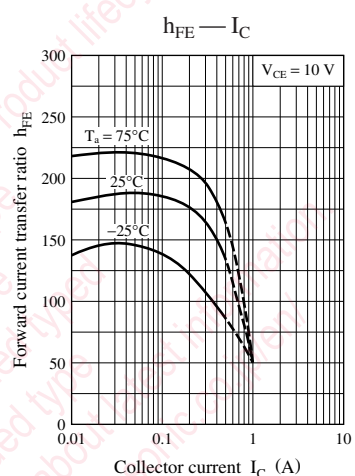
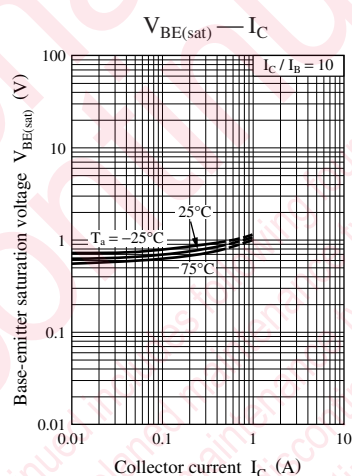
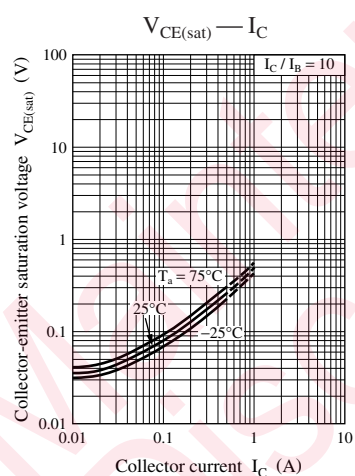
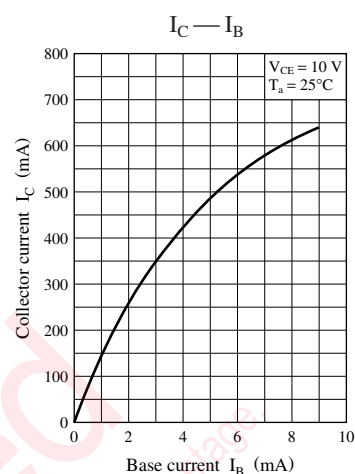
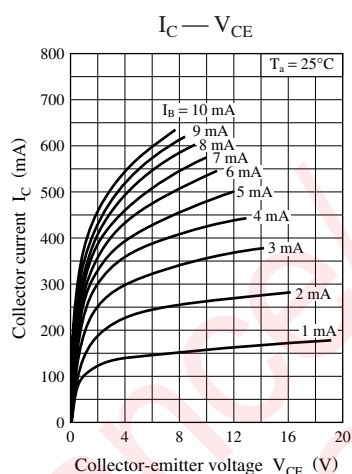
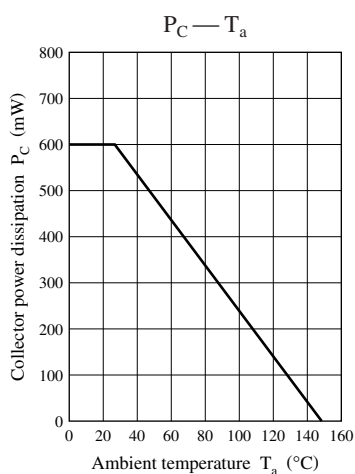
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10\ \mu\text{A}$ , $I_E = 0$	30			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2\ \text{mA}$ , $I_B = 0$	25			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10\ \mu\text{A}$ , $I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20\ \text{V}$ , $I_E = 0$			0.1	$\mu\text{A}$
Base-emitter saturation voltage	$I_{CEO}$	$V_{CE} = 20\ \text{V}$ , $I_B = 0$			1	$\mu\text{A}$
Forward current transfer ratio	$h_{FE1}$ *	$V_{CE} = 10\ \text{V}$ , $I_C = 10\ \text{mA}$	85		340	—
	$h_{FE2}$	$V_{CE} = 10\ \text{V}$ , $I_C = 500\ \text{mA}$	40	90		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 300\ \text{mA}$ , $I_B = 30\ \text{mA}$		0.35	0.6	V
Transition frequency	$f_T$	$V_{CB} = 10\ \text{V}$ , $I_E = -50\ \text{mA}$ , $f = 200\ \text{MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = 10\ \text{V}$ , $I_E = 0$ , $f = 1\ \text{MHz}$		6	15	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	Q	R	S
$h_{FE1}$	85 to 170	120 to 240	170 to 340

Note) The part number in the parenthesis shows conventional part number.



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